

FLASH MEMORY WITH HIGH-K DIELECTRIC MATERIAL
BETWEEN SUBSTRATE AND GATE

ABSTRACT OF THE DISCLOSURE

A flash memory cell and a method of forming the same are described. The flash memory cell may include a substrate having a source and a drain, a gate element, and a dielectric layer between the
5 substrate and the gate element. The dielectric layer includes a dielectric material having a dielectric constant that is greater than that of silicon dioxide.